

# isc N-Channel MOSFET Transistor

# **TK16N60W**

### • FEATURES

- Low drain-source on-resistance: R<sub>D</sub>s(on) ≤0.19Ω.
- Enhancement mode:
  Vth =2.7 to 3.7V (VDS = 10 V, ID=0.79mA)
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### DESCRITION

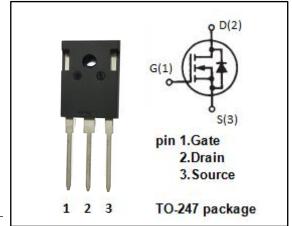
· Switching Voltage Regulators

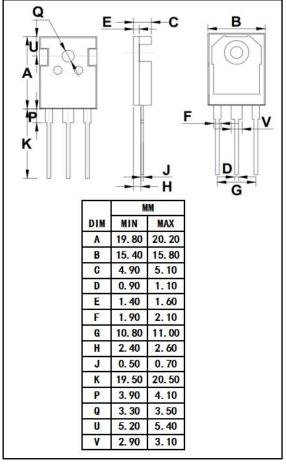
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>DSS</sub>	Drain-Source Voltage	600	V	
V <sub>G</sub> s	Gate-Source Voltage ±30			
I <sub>D</sub>	Drain Current-Continuous 15.8		Α	
І <sub>ОМ</sub>	Drain Current-Single Pulsed	63.2	Α	
P <sub>D</sub>	otal Dissipation @Tc=25°C 130		W	
Tj	Max. Operating Junction Temperature	150	$^{\circ}$ C	
T <sub>stg</sub>	Storage Temperature	-55~150	$^{\circ}$	

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.962	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V; I <sub>D</sub> =10mA	600			V
$V_{\text{GS(th)}}$	Gate Threshold Voltage	V <sub>DS</sub> =10V; I <sub>D</sub> =0.79mA	2.7		3.7	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> =7.9A			0.19	Ω
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> = 0V			±1	μА
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =600V; V <sub>GS</sub> = 0V			10	μА
$V_{SDF}$	Diode forward voltage	I <sub>DR</sub> =15.8A, V <sub>GS</sub> = 0 V			1.7	V

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